

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please cancel claim 4 without prejudice or disclaimer.

Please amend claims 3 and 6 as follows:

3. (Twice Amended) A group III nitride compound semiconductor device of a successively laminated structure comprising:

a substrate;

a buffer layer;

a first layer formed of $Al_aGa_bIn_{1-a-b}N$ ($0, a, 1, 0, b, 1, a+b, 1$); and

a second layer formed of $In_YGa_{1-Y}N$ ($0 < Y < 1$);

wherein said buffer layer is disposed between and in direct contact with both said substrate and said first layer, and said first layer is disposed between and in direct contact with both said buffer layer and said second layer, and

wherein a composition ratio of Al and In in said first layer is changed continuously or intermittently in a direction toward the second layer side from the buffer layer side so that a lattice constant of said first layer in a face brought into contact with said second layer becomes substantially equal to a lattice constant of said second layer.

6. (Amended) A group III nitride compound semiconductor device according to claim [4] 3, wherein the composition ratio of Al and In in said first layer is changed continuously or intermittently in the direction toward the second layer side from the buffer layer side so that a band gap of said first layer in a face brought into contact with said second layer becomes wider than a band gap of said second layer.